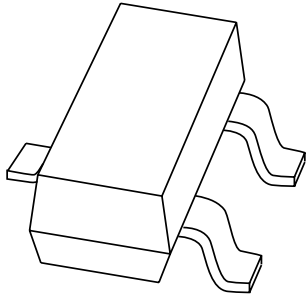


DATA SHEET



BAV99

High-speed double diode

Product specification
Supersedes data of 1999 May 11

2001 Oct 15

High-speed double diode

BAV99

FEATURES

- Small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 450 mA.

APPLICATIONS

- High-speed switching in thick and thin-film circuits.

DESCRIPTION

The BAV99 consists of two high-speed switching diodes connected in series, fabricated in planar technology, and encapsulated in the small SOT23 plastic SMD package.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
BAV99	A7*

Note

1. * = p: Made in Hong Kong.
* = t: Made in Malaysia.
* = W: Made in China.

PINNING

PIN	DESCRIPTION
1	anode
2	cathode
3	common connection

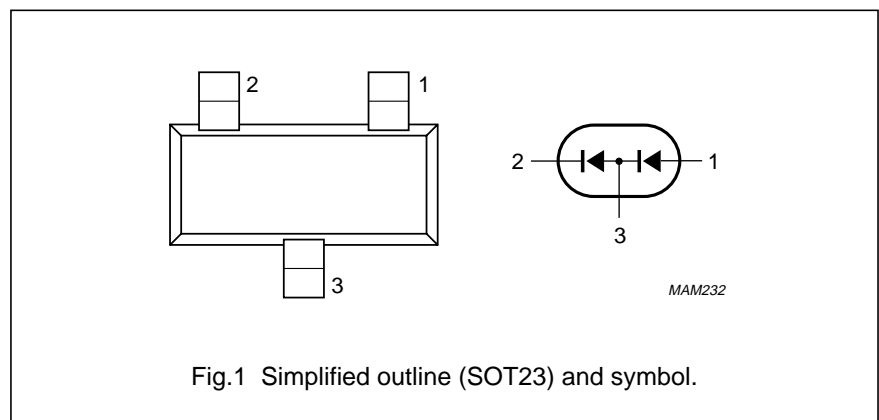


Fig.1 Simplified outline (SOT23) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V _{RRM}	repetitive peak reverse voltage		–	85	V
V _R	continuous reverse voltage		–	75	V
I _F	continuous forward current	single diode loaded; see Fig.2; note 1	–	215	mA
		double diode loaded; see Fig.2; note 1	–	125	mA
I _{FRM}	repetitive peak forward current		–	450	mA
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4			
		t = 1 μs	–	4	A
		t = 1 ms	–	1	A
		t = 1 s	–	0.5	A
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	–	250	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C

Note

1. Device mounted on an FR4 printed-circuit board.

High-speed double diode

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ELECTRICAL CHARACTERISTICS $T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
Per diode				
V_F	forward voltage	see Fig.3		
		$I_F = 1\text{ mA}$	715	mV
		$I_F = 10\text{ mA}$	855	mV
		$I_F = 50\text{ mA}$	1	V
I_R	reverse current	$I_F = 150\text{ mA}$	1.25	V
		see Fig.5		
		$V_R = 25\text{ V}$	30	nA
		$V_R = 75\text{ V}$	1	μA
C_d	diode capacitance	$V_R = 25\text{ V}; T_j = 150\text{ °C}$	30	μA
		$V_R = 75\text{ V}; T_j = 150\text{ °C}$	50	μA
t_{rr}	reverse recovery time	$f = 1\text{ MHz}; V_R = 0$; see Fig.6	1.5	pF
t_{fr}	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}$; $R_L = 100\ \Omega$; measured at $I_R = 1\text{ mA}$; see Fig.7	4	ns
V_{fr}	forward recovery voltage	when switched from $I_F = 10\text{ mA}$; $t_r = 20\text{ ns}$; see Fig.8	1.75	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point		360	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

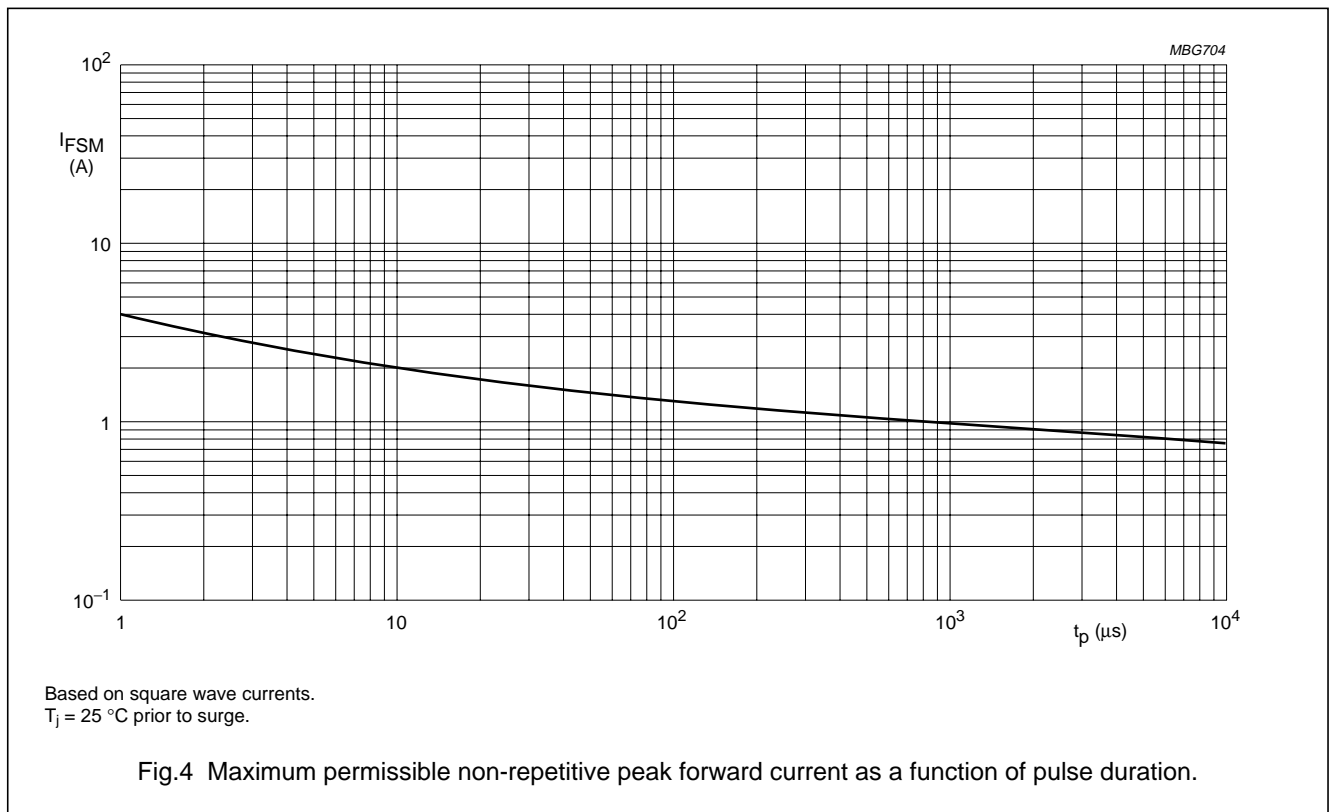
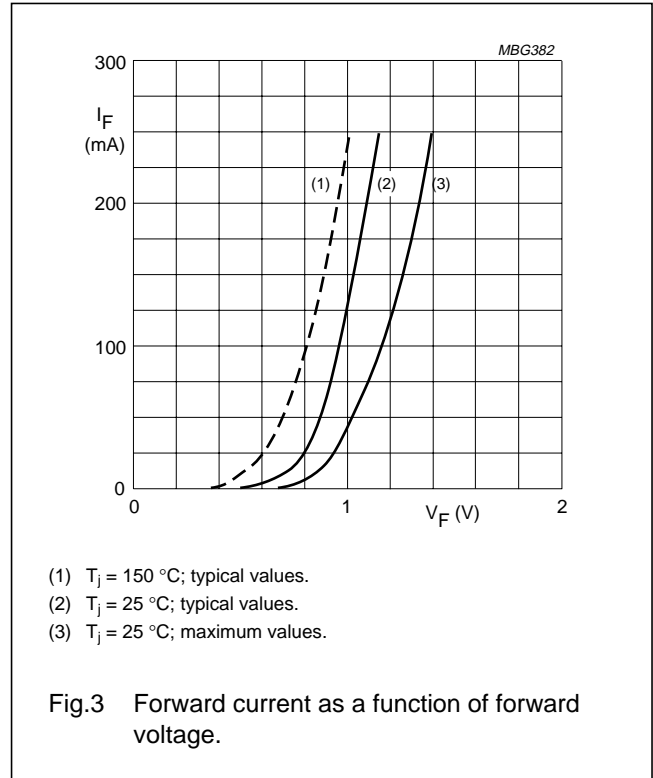
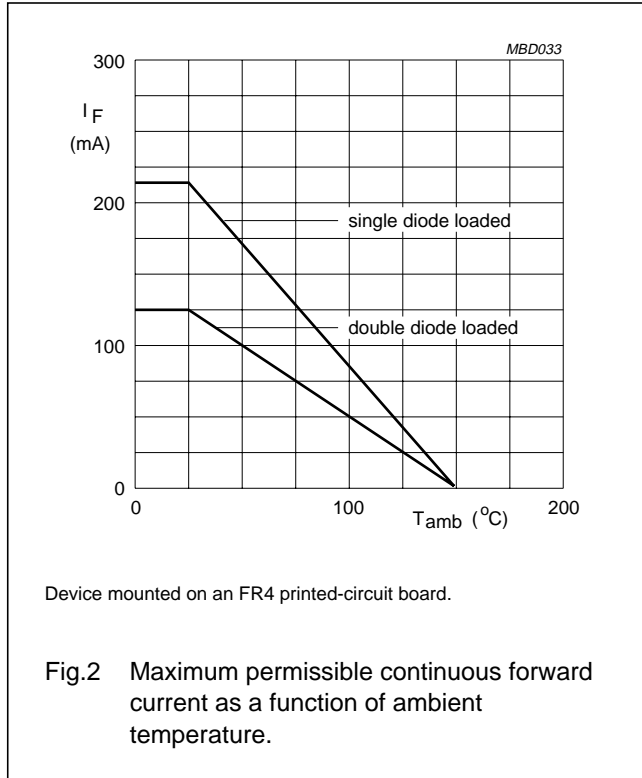
Note

1. Device mounted on an FR4 printed-circuit board.

High-speed double diode

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GRAPHICAL DATA



High-speed double diode

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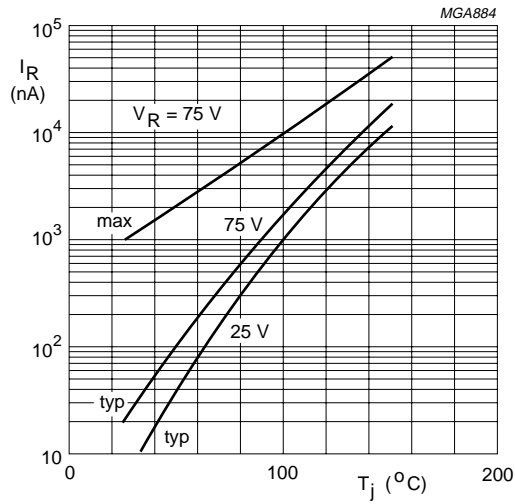
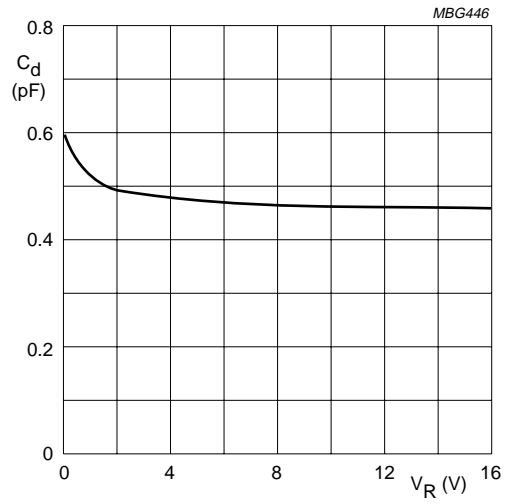


Fig.5 Reverse current as a function of junction temperature.

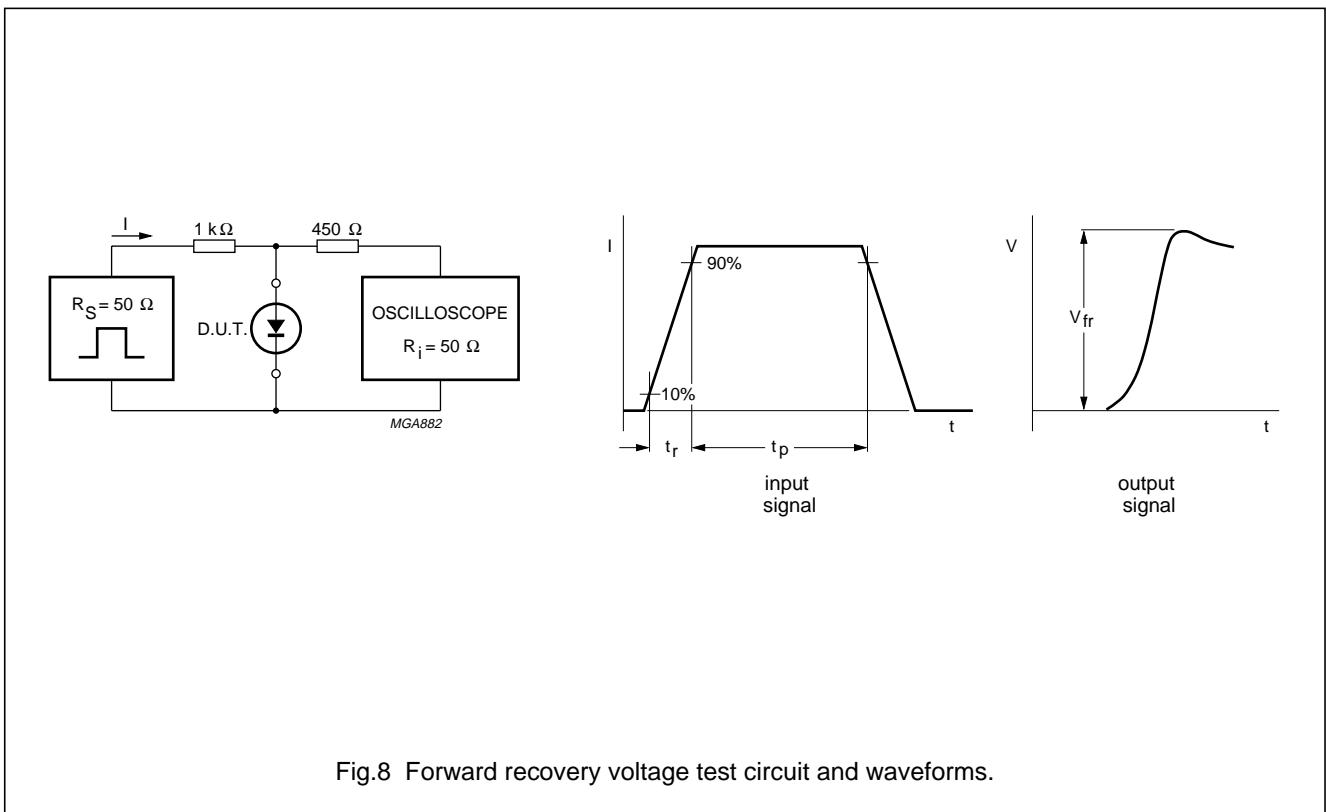
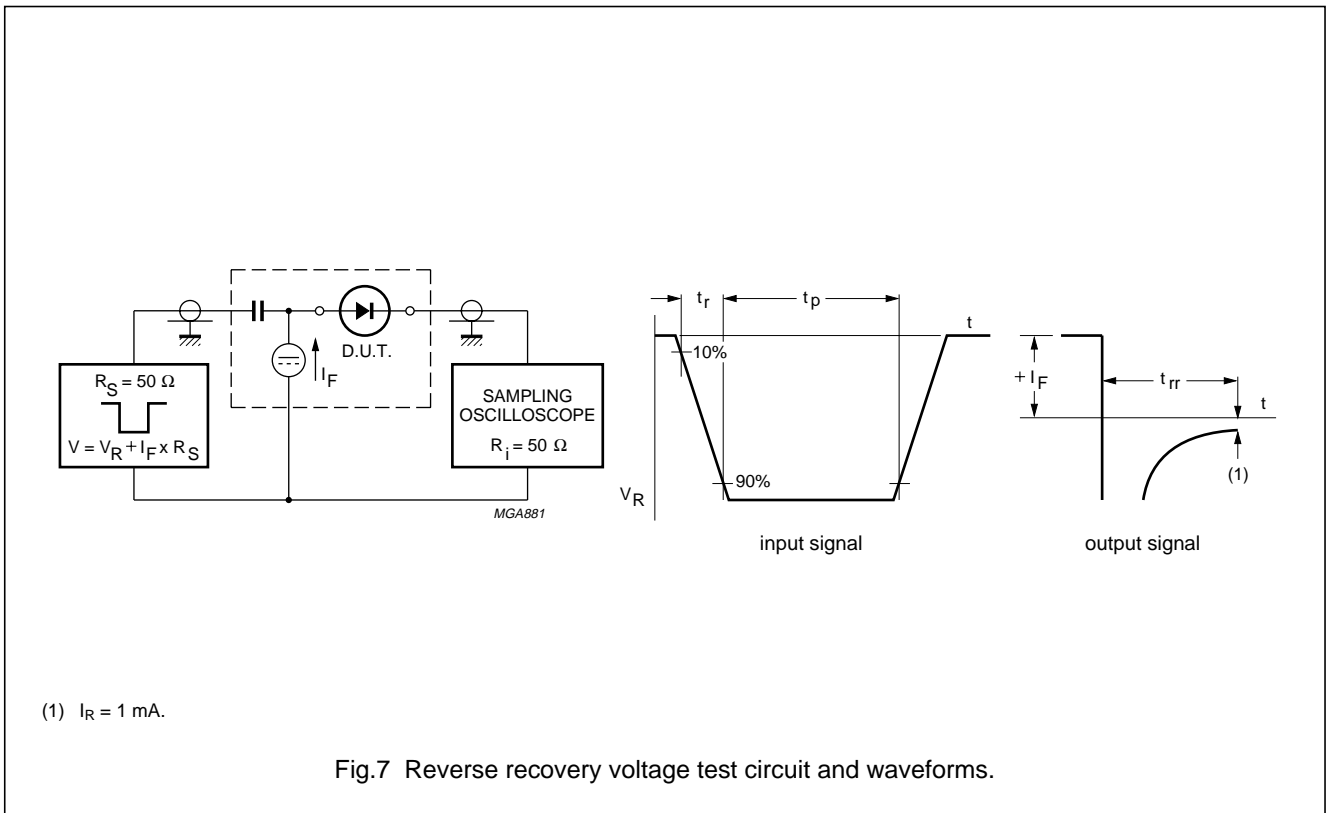


$f = 1$ MHz; $T_j = 25$ °C.

Fig.6 Diode capacitance as a function of reverse voltage; typical values.

High-speed double diode

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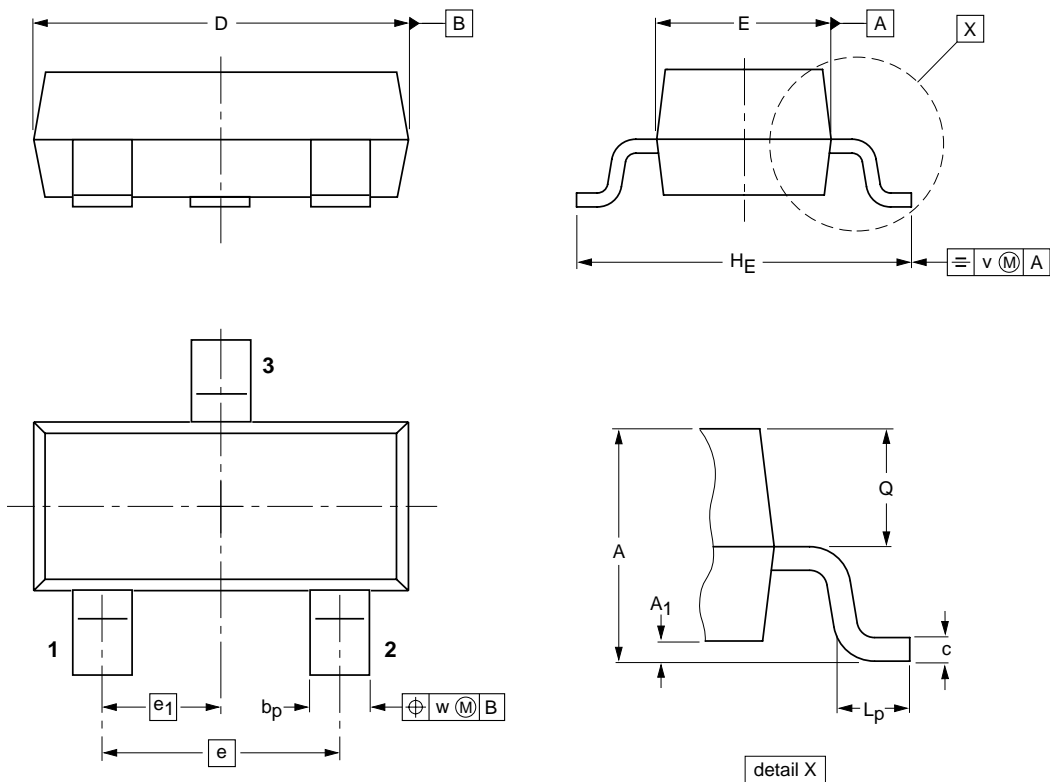
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT23		TO-236AB			97-02-28 99-09-13

High-speed double diode

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DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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NOTES

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